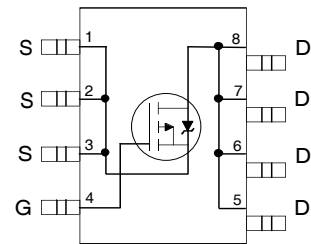


General Description:

The IRF7204TR is the single P-Channel logic enhancement mode power field effect transistors to provide excellent $R_{DS(on)}$, low gate charge and low gate resistance. It's up to -30V operation voltage is well suited in switching mode power supply, SMPS, notebook computer power management and other battery powered circuits.



Top View

Features:

- $R_{DS(ON)} < 55m @ V_{GS} = 10V$
- $R_{DS(ON)} < 90m @ V_{GS} = 4.5V$
- Super high density cell design for extremely low
- $R_{DS(ON)}$ Exceptional on-resistance and maximum DC current

Applications:

- Switching power supply, SMPS
- Battery Powered System
- DC/DC Converter
- DC/AC Converter
- Load Switch

Absolute Maximum Ratings ($T_A = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	-5.1	A
Drain Current-Pulsed (Note 1)	I_{DM}	-20	A
Maximum Power Dissipation	P_D	2.5	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	50	$^\circ C/W$
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Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA	-30	-33	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-24V, V _{GS} =0V	-	-	-1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-1		-2.0	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-5.1A	-	43	55	mΩ
		V _{GS} =-4.5V, I _D =-4.2A	-	62	90	mΩ
Forward Transconductance	g _{FS}	V _{DS} =-15V, I _D =-4.5A	4	7	-	S
Dynamic Characteristics (Note 4)						
Input Capacitance	C _{iss}	V _{DS} =-15V, V _{GS} =0V, F=1.0MHz	-	520	-	PF
Output Capacitance	C _{oss}		-	130	-	PF
Reverse Transfer Capacitance	C _{rss}		-	70	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =-15V, I _D =-1A, V _{GS} =-10V, R _{GEN} =6Ω	-	7	-	nS
Turn-on Rise Time	t _r		-	13	-	nS
Turn-Off Delay Time	t _{d(off)}		-	14	-	nS
Turn-Off Fall Time	t _f		-	9	-	nS
Total Gate Charge	Q _g	V _{DS} =-15V, I _D =-5.1A, V _{GS} =-10V	-	11	-	nC
Gate-Source Charge	Q _{gs}		-	2.2	-	nC
Gate-Drain Charge	Q _{gd}		-	3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =-5.1A	-	-	-1.2	V

Typical Electrical and Thermal Characteristics

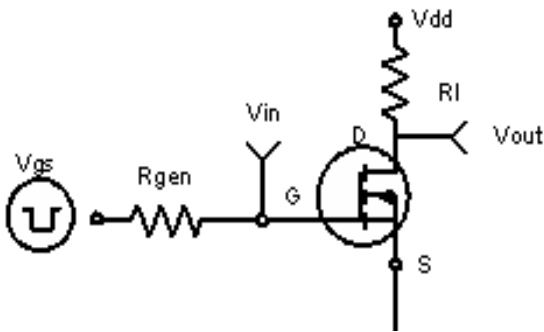


Figure 1: Switching Test Circuit

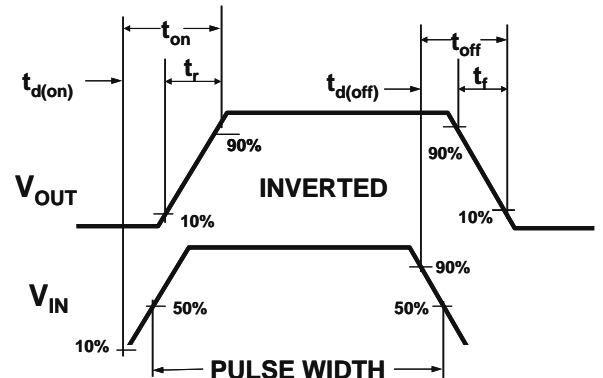
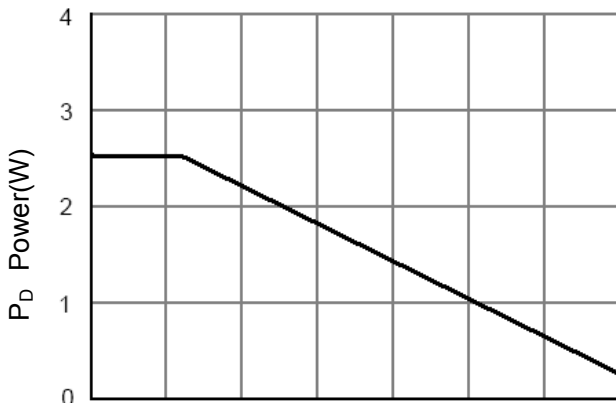
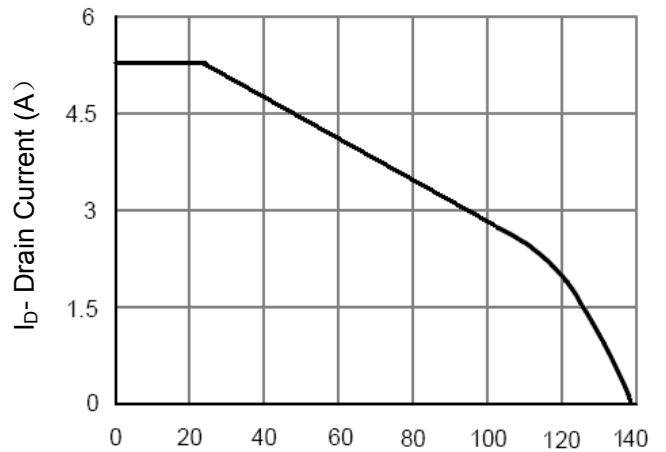


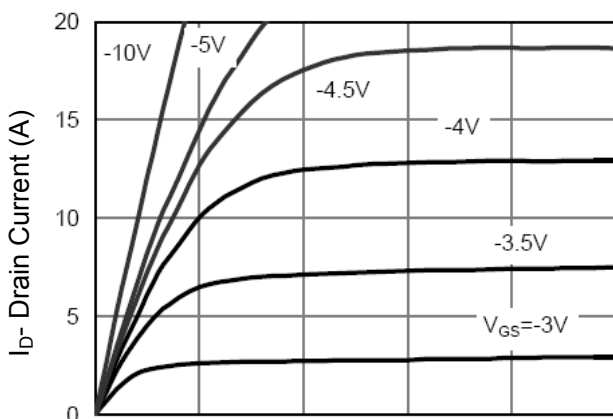
Figure 2: Switching Waveforms



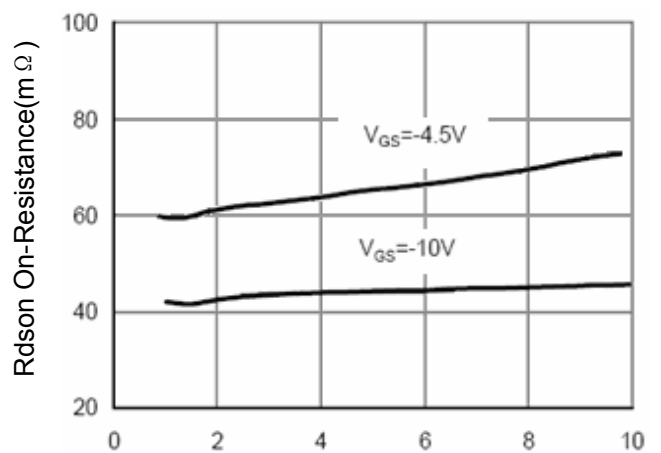
T_J-Junction Temperature(°C)
Figure 3 Power Dissipation



T_J-Junction Temperature(°C)
Figure 4 Drain Current



V_{ds} Drain-Source Voltage (V)
Figure 5 Output Characteristics



I_D- Drain Current (A)
Figure 6 Drain-Source On-Resistance

Figure 5 Output Characteristics

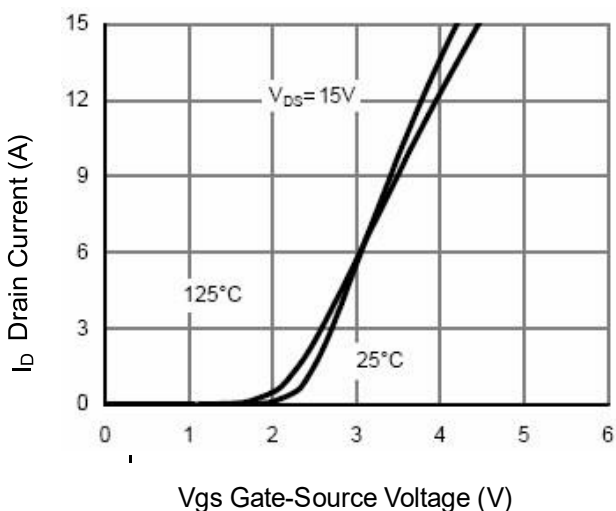


Figure 7 Transfer Characteristics

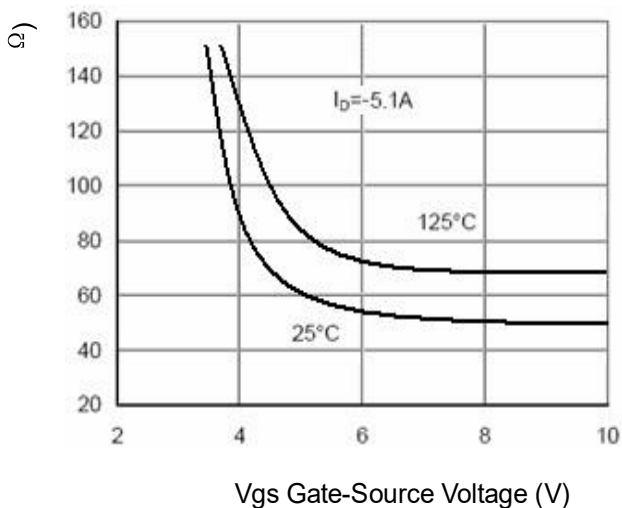


Figure 9 Rds(on) vs Vgs

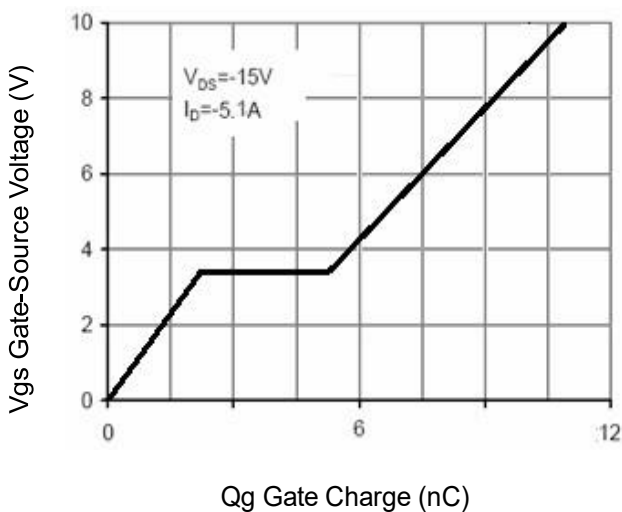


Figure 11 Gate Charge

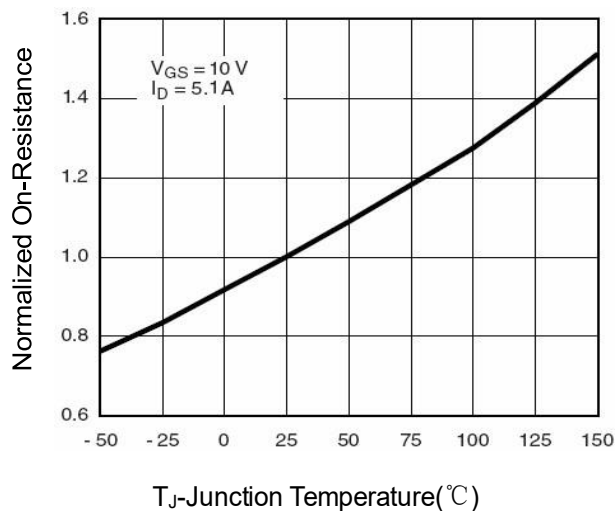


Figure 10 Capacitance vs Vds

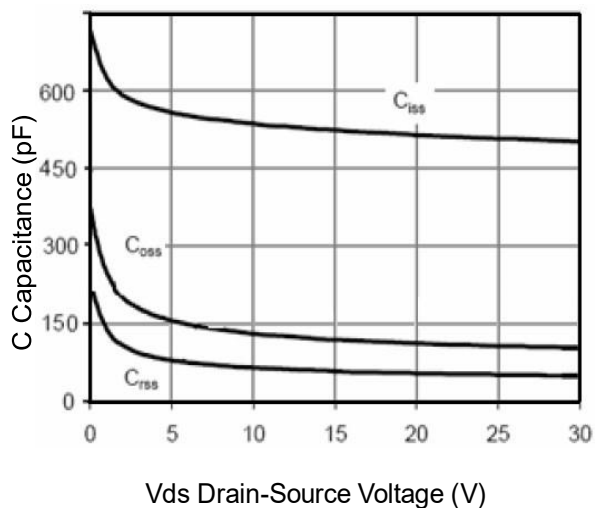
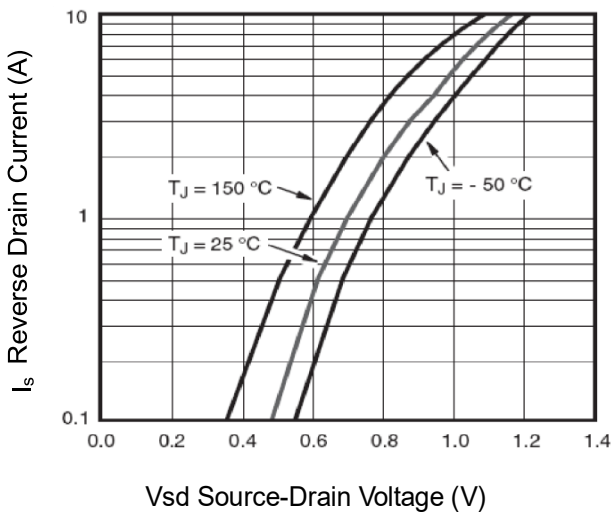


Figure 12 Source- Drain Diode Forward



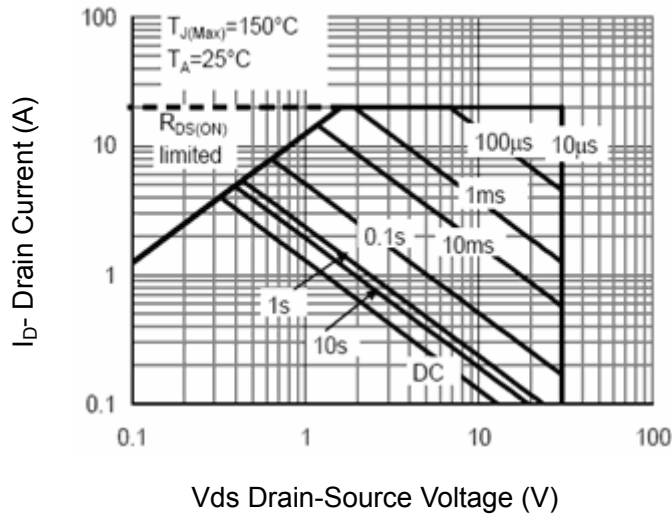


Figure 13 Safe Operation Area

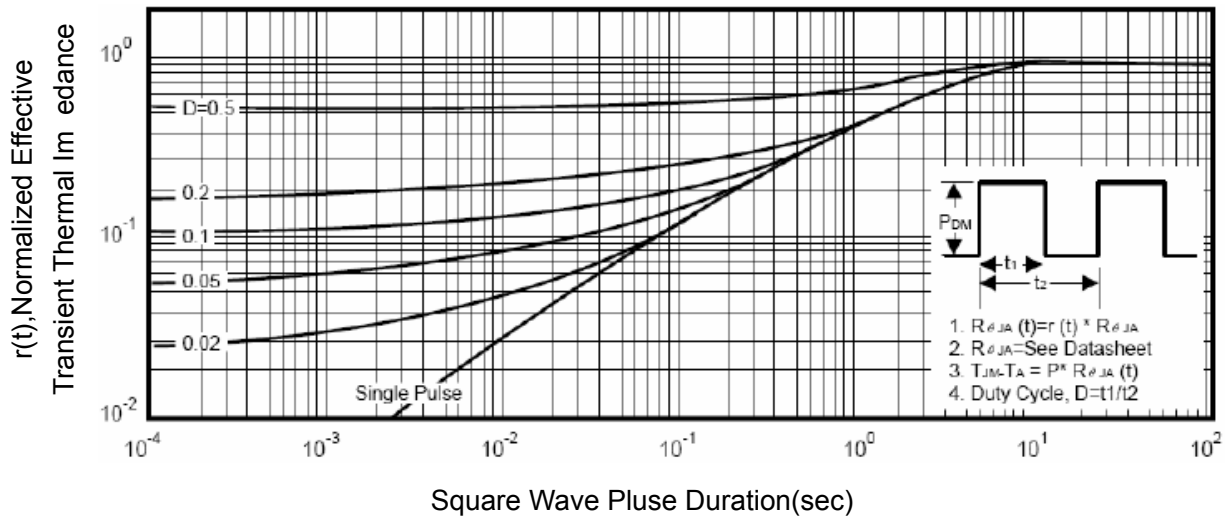
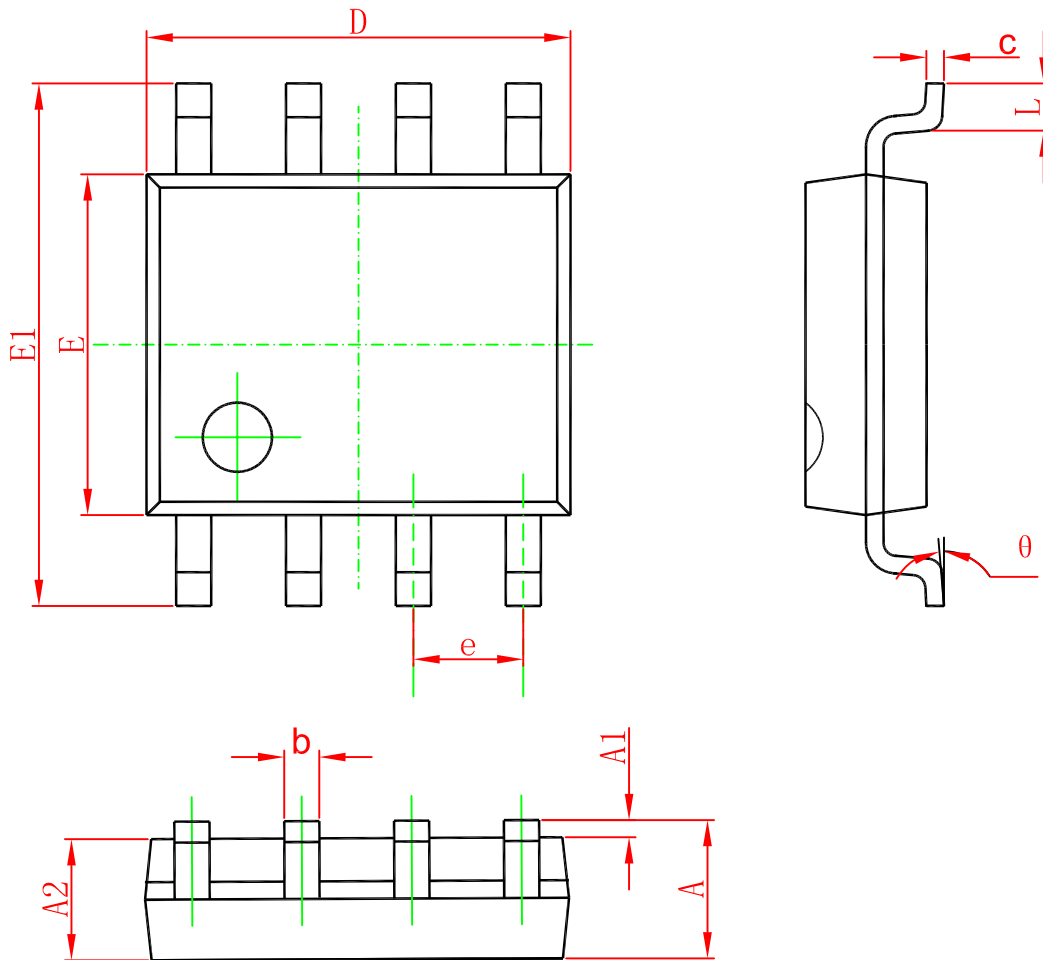


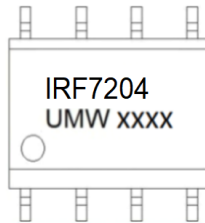
Figure 14 Normalized Maximum Transient Thermal Impedance

SOP-8



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

Marking



Ordering information

Order code	Package	Baseqty	Deliverymode
UMW IRF7204TR	SOP-8	3000	Tape and reel